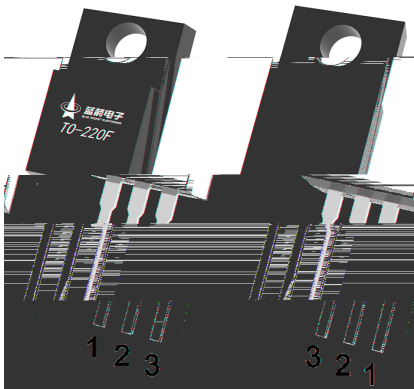
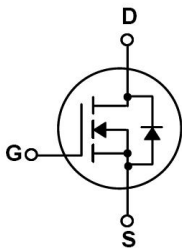


SiC

$\leq$	Ω	Ω
$\leq$	Ω	Ω

LED	PD	PC
-----	----	----



						μ
						Ω
						μ



		Ω μ				
-						μ
-						
						Ω

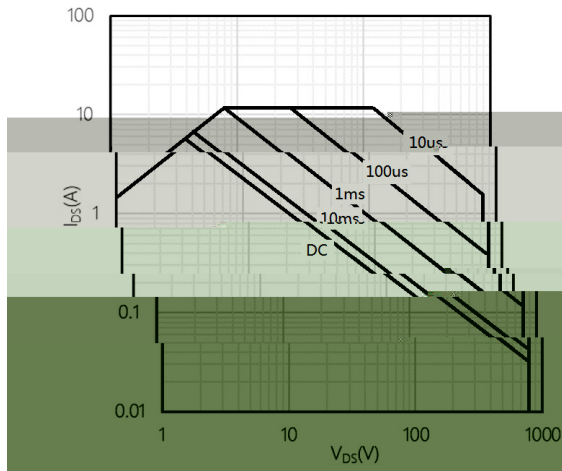


Fig1. Safe operating area (SOA)

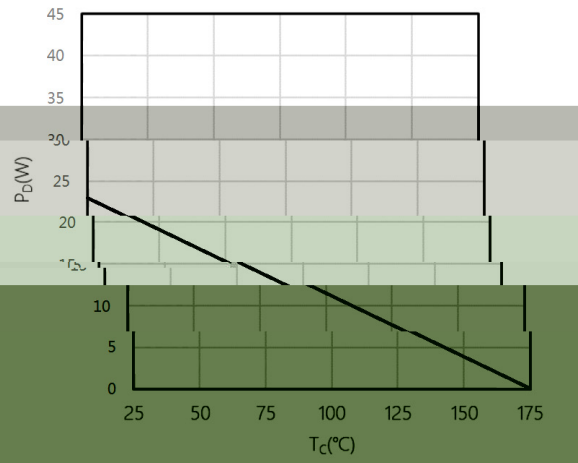


Fig2. Power dissipation

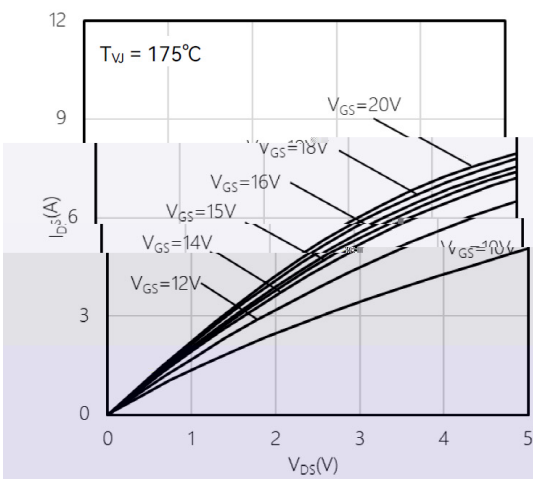
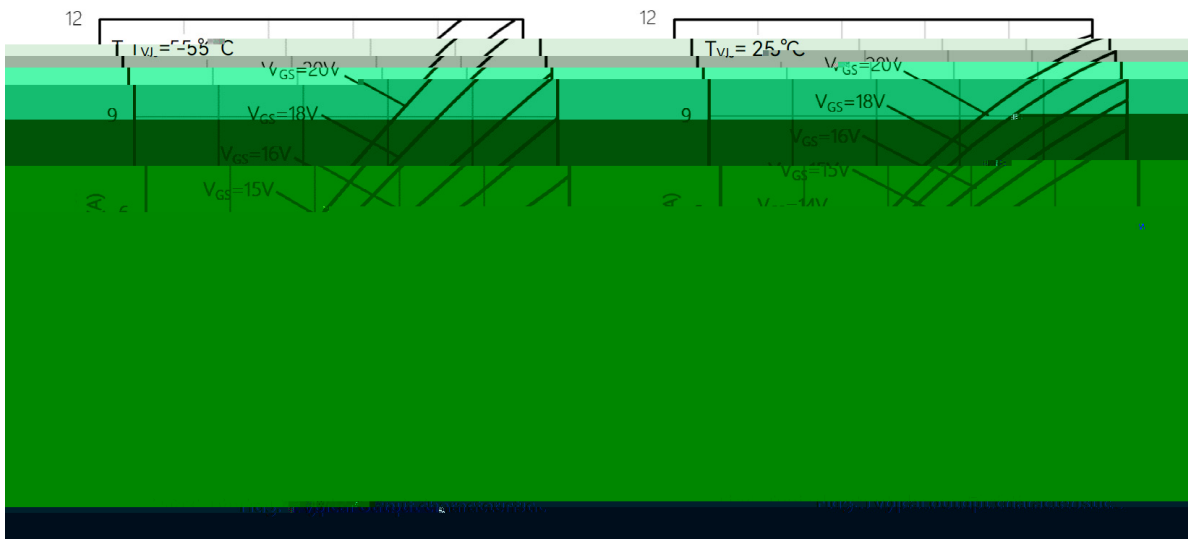


Fig5. Typical output characteristic

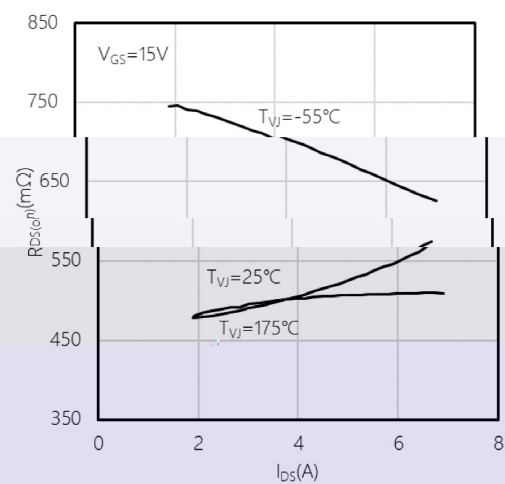


Fig6. Typical on-state resistance as a function of drain current

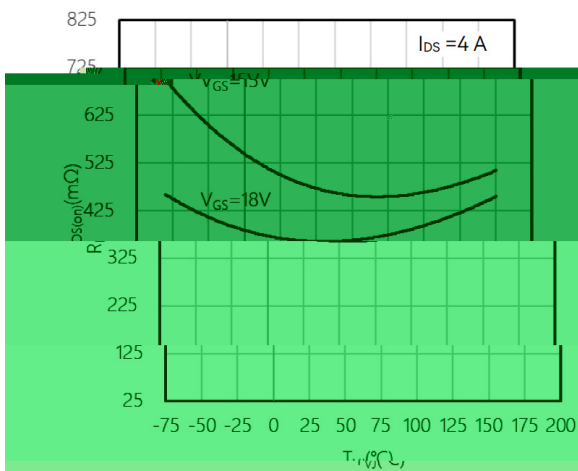


Fig7. Typical on-state resistance as a function of temperature

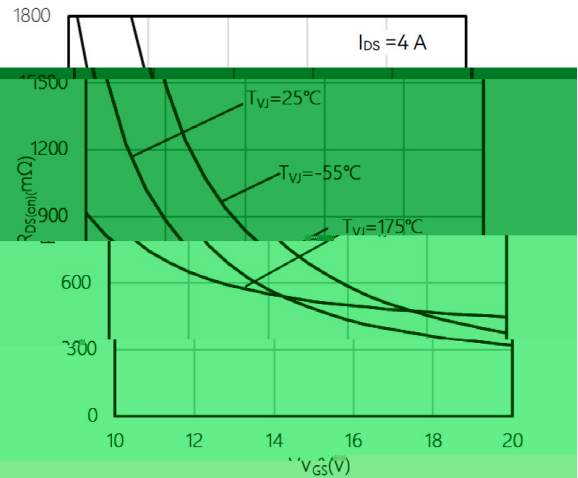


Fig8. Typical on-state resistance as a function of V_{GS}

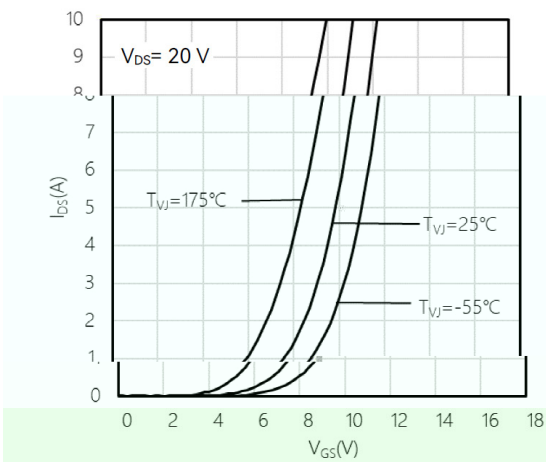


Fig9. Typical transfer characteristic

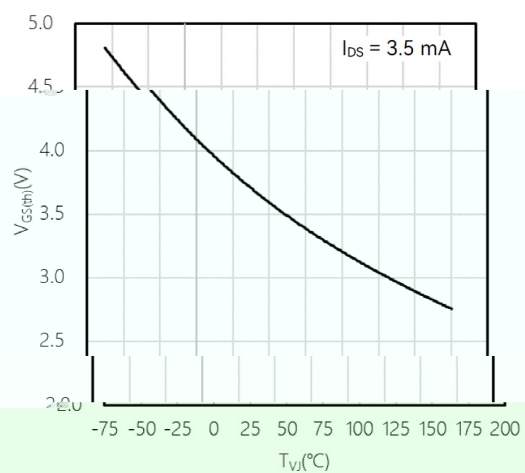


Fig10. Typical gate reverse threshold voltage as a function of junction temperature

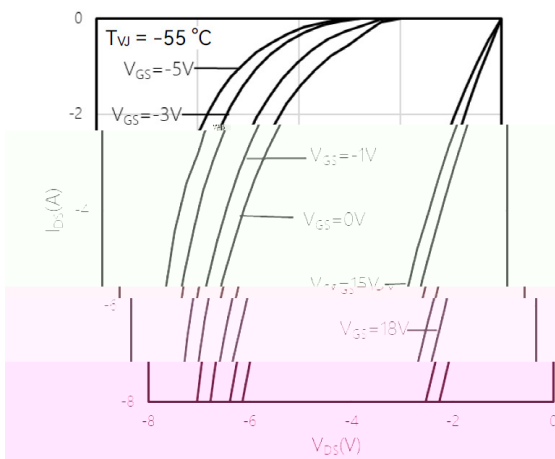


Fig11. Typical reverse drain current as function of reverse drain voltage

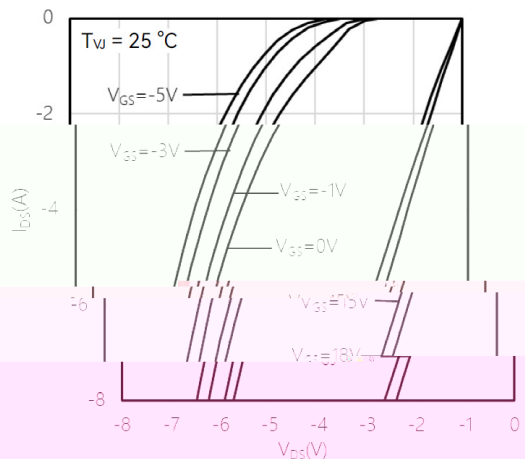


Fig12. Typical reverse drain current as function of reverse drain voltage

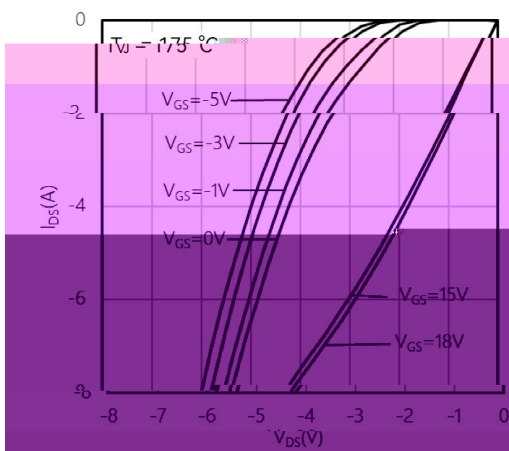


Fig13. Typical reverse drain current as function

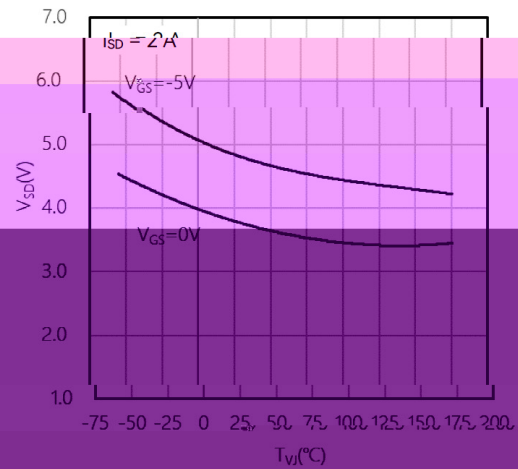


Fig14. Typical reverse drain voltage as

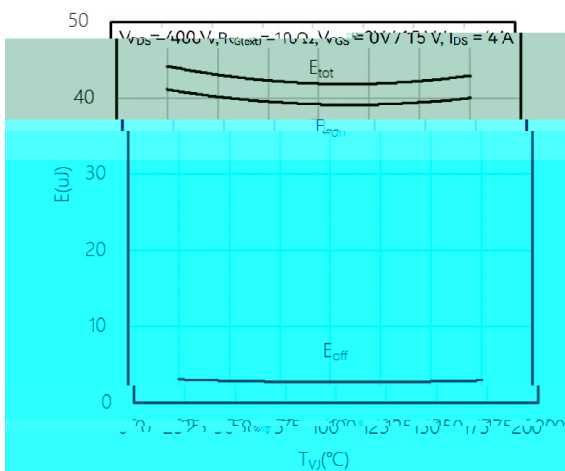


Fig15. Typical switching energy as a function of junction temperature, 2nd device own body diode: $V_{GS} = 0\text{V}$

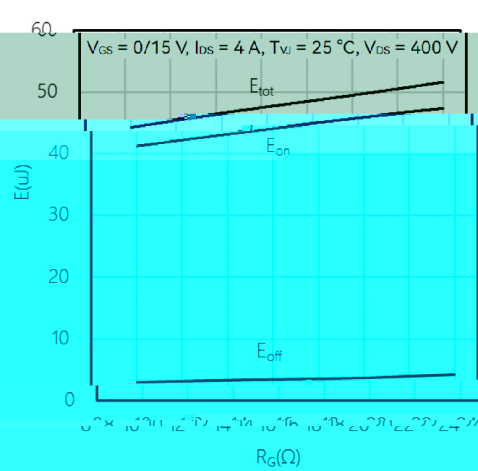


Fig16. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: $V_{GS} = 0\text{V}$

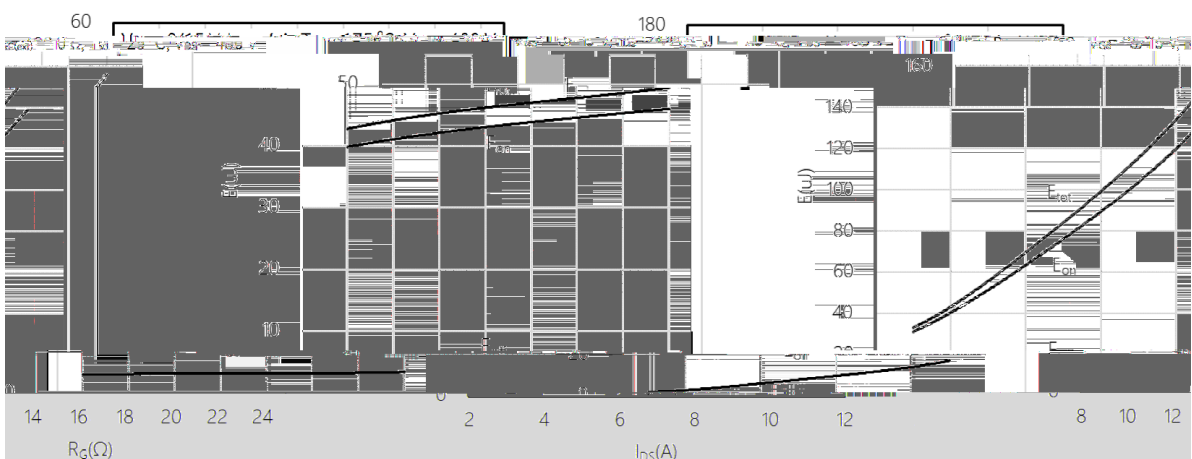


Fig17. Typical switching energy losses as a function of gate resistance, 2nd device own body diode: $V_{GS} = 0\text{V}$

Fig18. Typical switching energy losses as a function of I_{DS} , 2nd device own body diode: $V_{GS} = 0\text{V}$

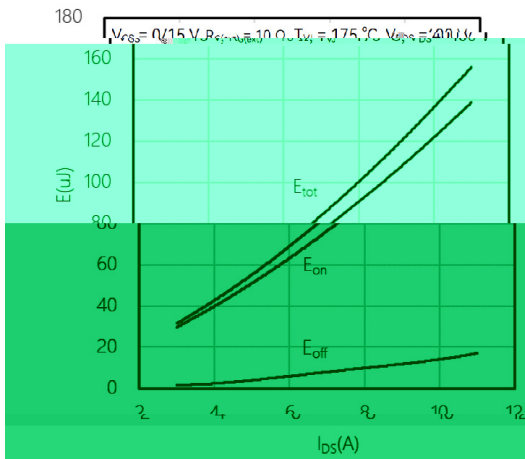


Fig19. Typical switching energy losses as a function of I_{DS} .

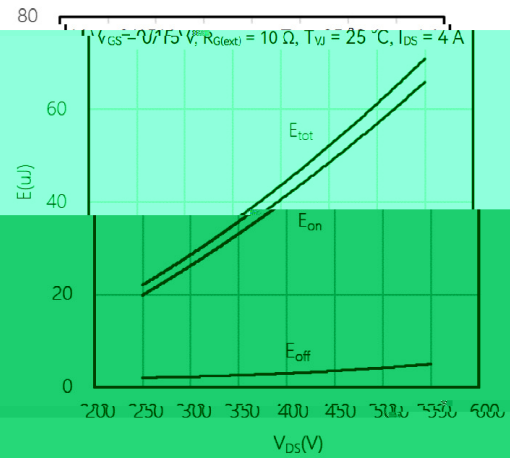


Fig20. Typical switching energy losses as a function of V_{DS} .

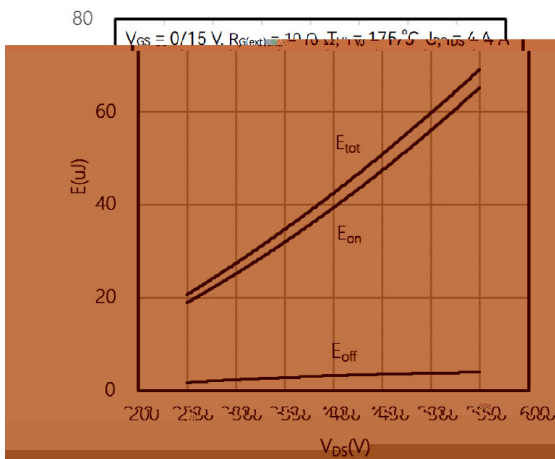


Fig21. Typical switching energy losses as a function of V_{DS} .

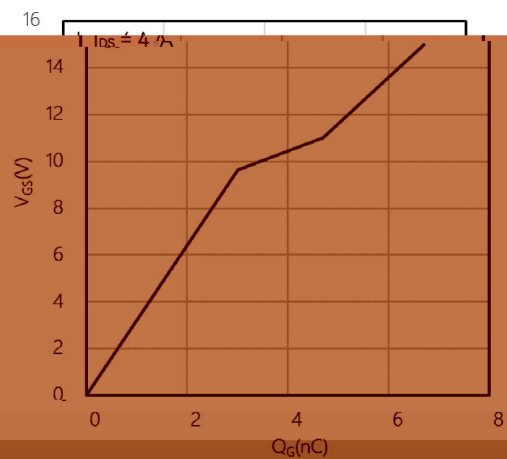


Fig22. Typical gate charge.

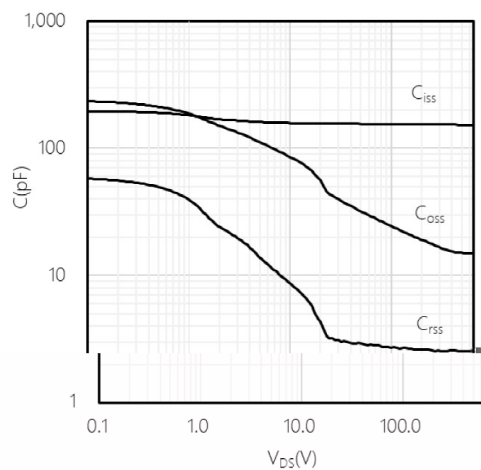


Fig23. Typical capacitance as a function of V_{DS} .

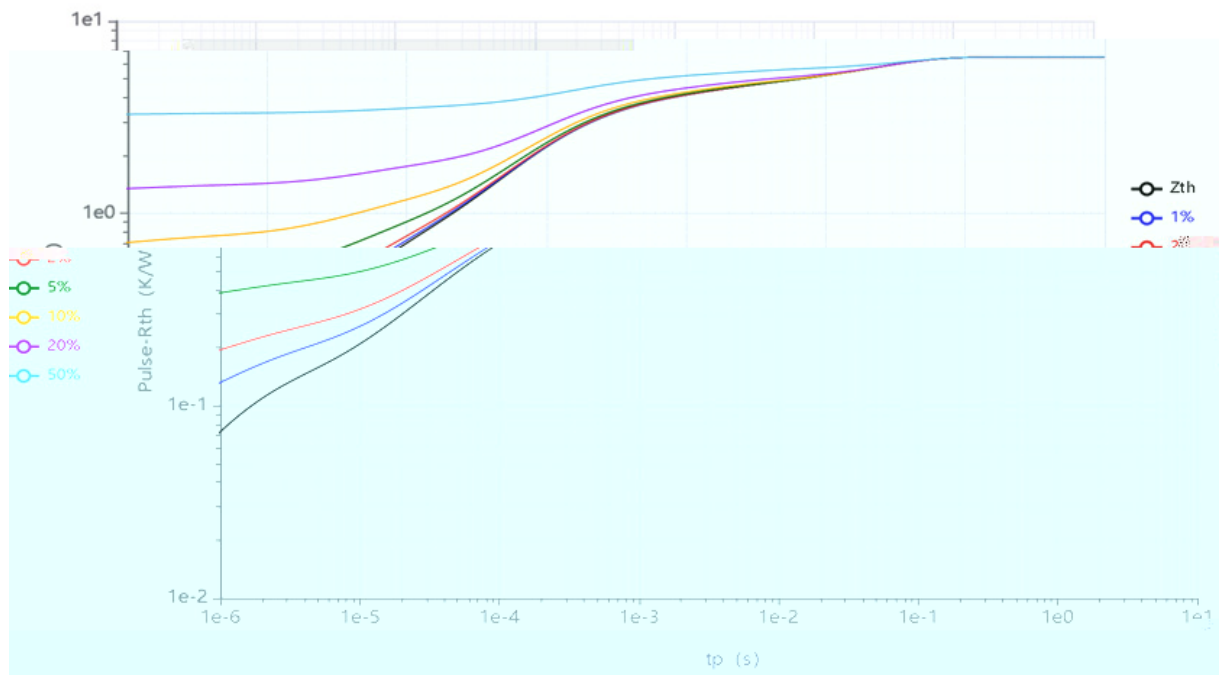
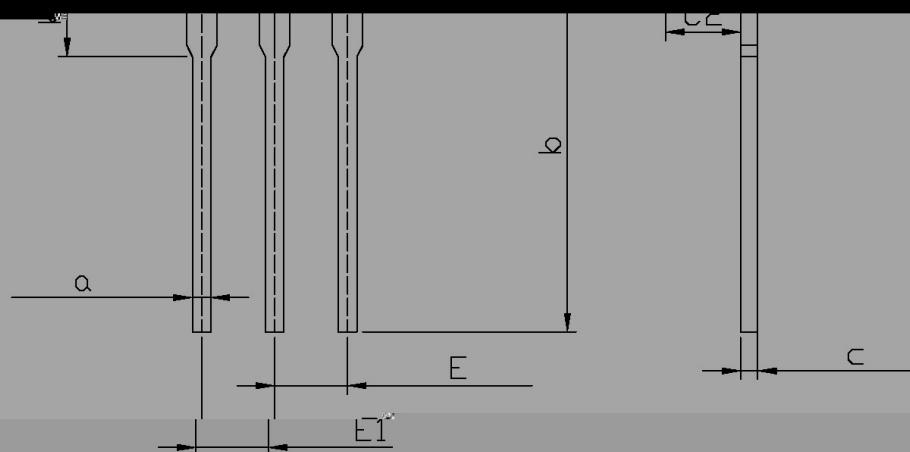
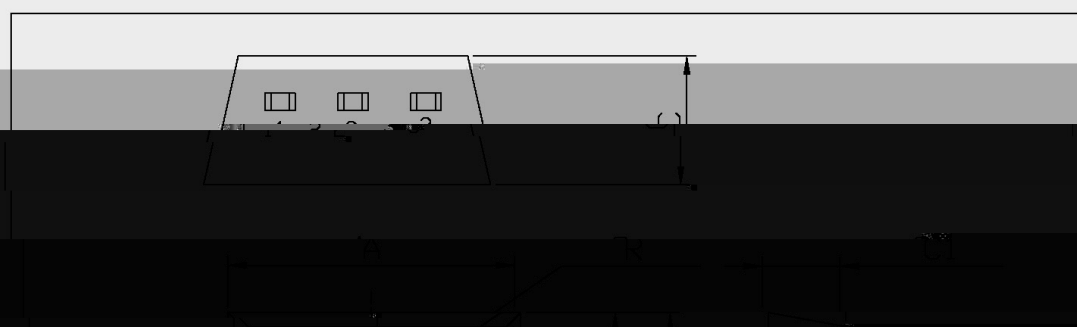


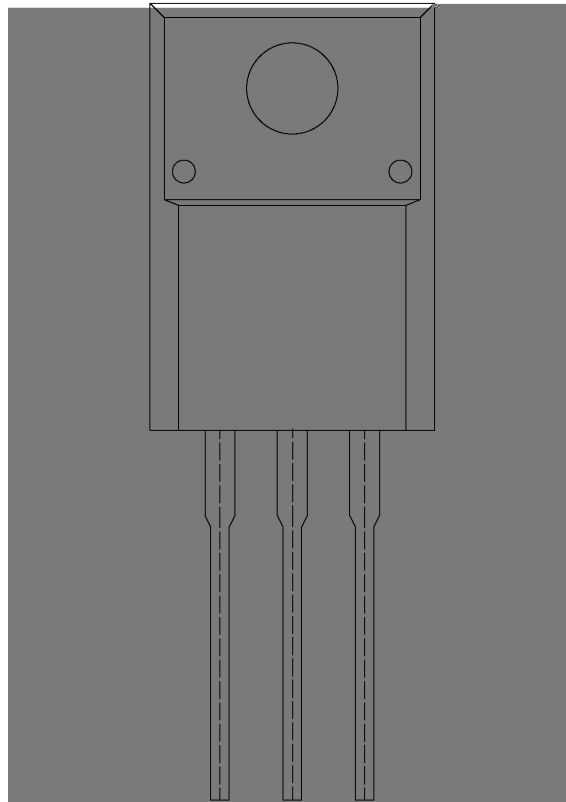
Fig24. Transient thermal resistance (MOSFET)

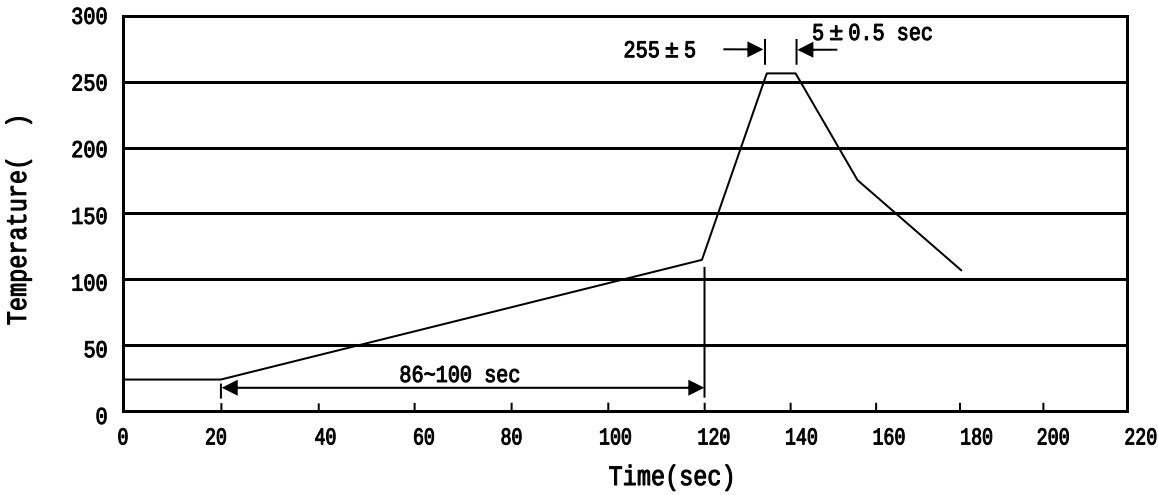
T0-220F

单位: mm



Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
C	4.3	4.7	b1	2.9	3.9
A	9.7	10.3	a	0.55	0.75
B	14.7	15.3	E	2.29	2.79
D	2.8	3.2	F	1.27	1.52





± ± ± ±

± ± °C

	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box

	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box